

COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR
Features

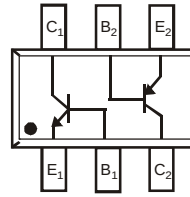
- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in one package
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **"Green" Device (Notes 3 and 4)**



Top View

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



Device Schematic

Maximum Ratings, NPN Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Emitter Current	I _{EM}	200	mA

Maximum Ratings, PNP Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Emitter Current	I _{EM}	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1) @ T _A = 25°C Total Device	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 1) @ T _A = 25°C	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants

Electrical Characteristics, NPN Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 5)	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 5)	$V_{(BR)CEO}$	45	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage (Note 5)	$V_{(BR)EBO}$	6	—	—	V	$I_E = 1\mu\text{A}, I_C = 0$
DC Current Gain (Note 5)	h_{FE}	200	290	450	—	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage (Note 5)	$V_{CE(SAT)}$	—	90 200	250 600	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 5)	$V_{BE(SAT)}$	—	700 900	—	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Voltage (Note 5)	$V_{BE(ON)}$	580 —	660 —	700 720	mV	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$ $V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$
Collector-Cutoff Current (Note 5)	I_{CBO} I_{CBO}	— —	— —	15 5.0	nA μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}, T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	300	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	3.5	6.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$
Noise Figure	NF	—	2.0	10	dB	$V_{CE} = 5\text{V}, I_C = 200\mu\text{A}, R_G = 2.0\text{k}\Omega$, $f = 1.0\text{kHz}, \Delta f = 200\text{Hz}$

Electrical Characteristics, PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 5)	$V_{(BR)CBO}$	-50	—	—	V	$I_C = -10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 5)	$V_{(BR)CEO}$	-45	—	—	V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage (Note 5)	$V_{(BR)EBO}$	-5	—	—	V	$I_E = -1\mu\text{A}, I_C = 0$
DC Current Gain (Note 5)	h_{FE}	220	290	475	—	$V_{CE} = -5.0\text{V}, I_C = -2.0\text{mA}$
Collector-Emitter Saturation Voltage (Note 5)	$V_{CE(SAT)}$	—	-75 -250	-300 -650	mV	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$ $I_C = -100\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 5)	$V_{BE(SAT)}$	—	-700 -850	— -950	mV	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$ $I_C = -100\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Voltage (Note 5)	$V_{BE(ON)}$	-600 —	-650 —	-750 -820	mV	$V_{CE} = -5.0\text{V}, I_C = -2.0\text{mA}$ $V_{CE} = -5.0\text{V}, I_C = -10\text{mA}$
Collector-Cutoff Current (Note 5)	I_{CBO} I_{CBO}	— —	— —	-15 -4.0	nA μA	$V_{CB} = -30\text{V}$ $V_{CB} = -30\text{V}, T_A = 150^\circ\text{C}$
Gain Bandwidth Product	f_T	100	200	—	MHz	$V_{CE} = -5.0\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$
Collector-Base Capacitance	C_{CBO}	—	3	4.5	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}$
Noise Figure	NF	—	—	10	dB	$V_{CE} = -5\text{V}, I_C = -200\mu\text{A}, R_G = 2.0\text{k}\Omega$, $f = 1.0\text{kHz}, \Delta f = 200\text{Hz}$

Notes: 5. Short duration pulse test used to minimize self-heating effect.

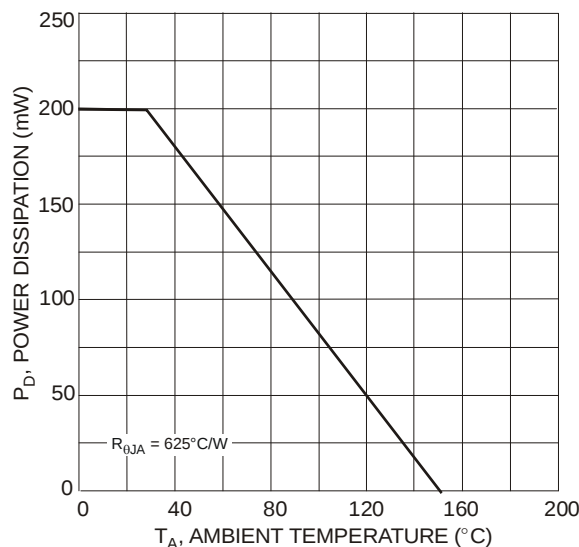


Fig. 1 Power Dissipation vs. Ambient Temperature
(Total Device, Note 1)

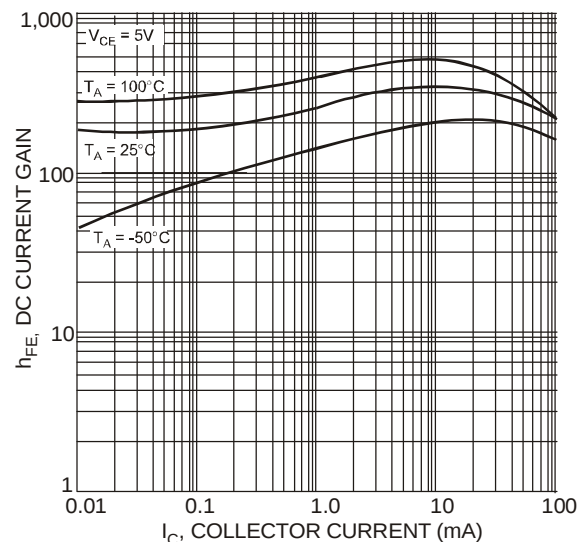


Fig. 2 Typical DC Current Gain vs. Collector Current (NPN)

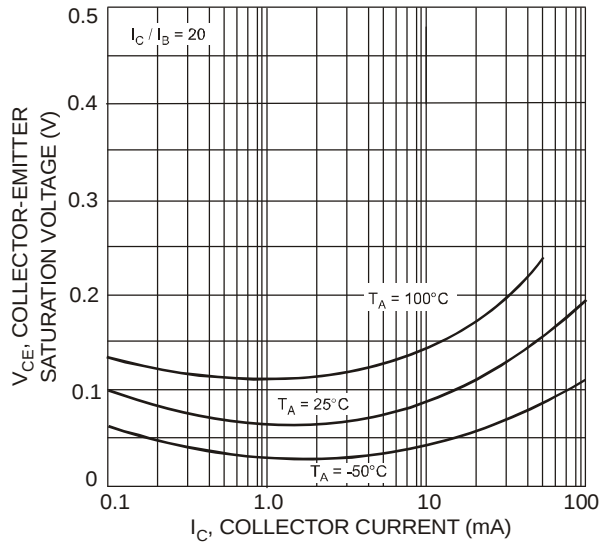


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current (NPN)

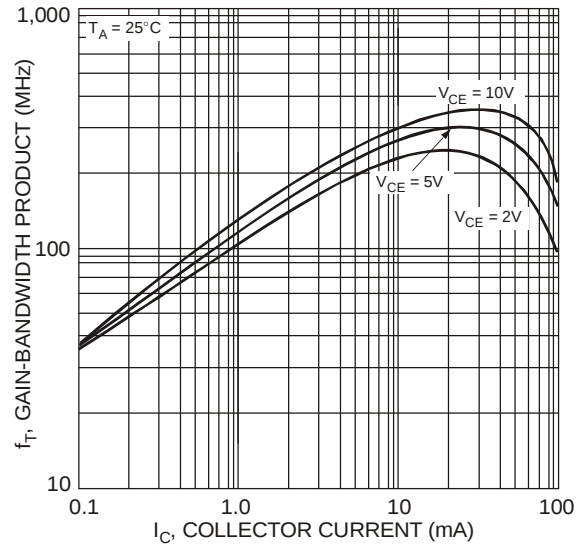


Fig. 4 Typical Gain-Bandwidth Product vs. Collector Current (NPN)

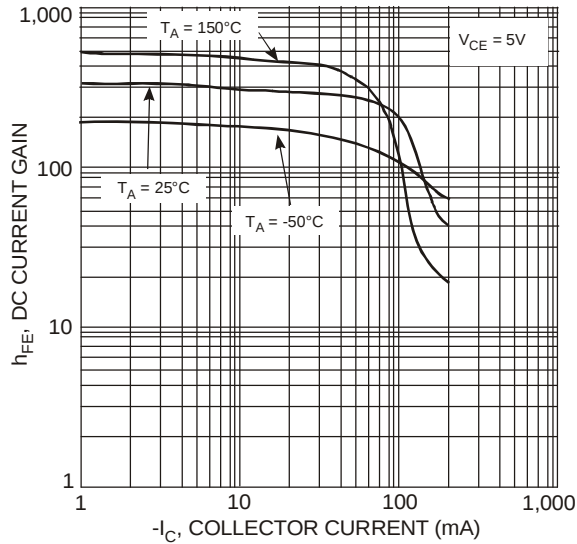


Fig. 5 Typical DC Current Gain vs. Collector Current (PNP)

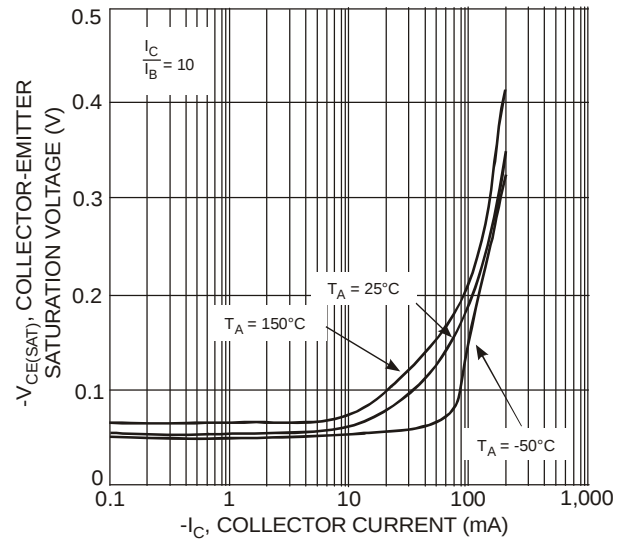


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current (PNP)

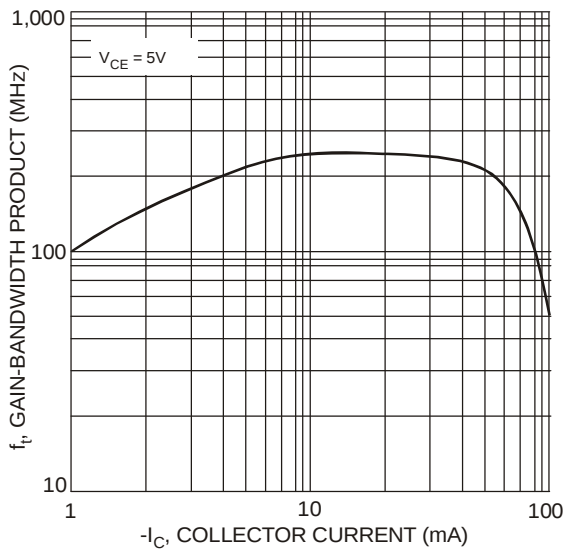


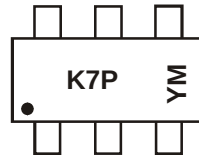
Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current (PNP)

Ordering Information (Note 6)

Part Number	Case	Packaging
BC847PN-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



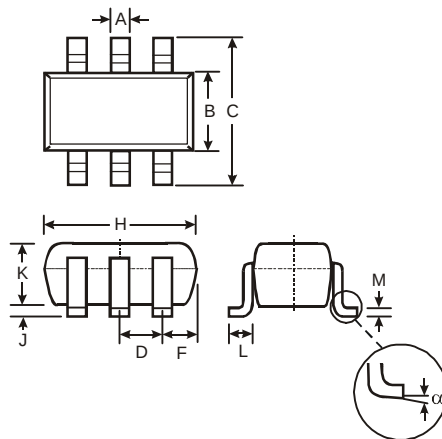
K7P = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: T = 2006)
 M = Month (ex: 9 = September)

Date Code Key

Year	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	M	N	P	R	S	T	U	V	W	X	Y	Z	A	B	C

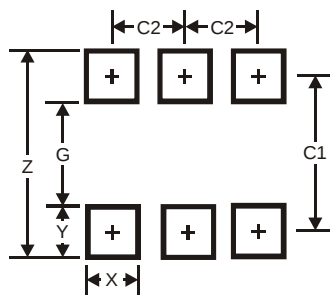
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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